Andrei A Gismatulin

List of Publications by Year
in descending order

32 papers	313 citations	840776 11 h-index	888059 17 g-index
32 all docs	32 docs citations	32 times ranked	320 citing authors

#	Article	IF	Citations
1	Charge Transport Mechanism in a PECVD Deposited Low-k SiOCH Dielectric. Journal of Electronic Materials, 2022, 51, 2521-2527.	2.2	1
2	Charge transport mechanism in the metalâ€“nitrideâ€“oxideâ€“silicon forming-free memristor structure. Chaos, Solitons and Fractals, 2021, 142, 110458.	5.1	6
3	Charge Transport Mechanism and Trap Origin in Methylâ€Terminated Organosilicate Glass Lowâ€Îº Dielectrics. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000654.	1.8	2
4	Charge Transport Mechanism in Atomic Layer Deposited Oxygenâ€Deficient TaO x Films. Physica Status Solidi (B): Basic Research, 2021, 258, 2000432.	1.5	4
5	Charge transport mechanism in the forming-free memristor based on silicon nitride. Scientific Reports, 2021, 11, 2417.	3.3	21
6	Bipolar conductivity in ferroelectric La:HfZrO films. Applied Physics Letters, 2021, 118, .	3.3	5
7	Memory Properties of SiOx- and SiNx-Based Memristors. Nanobiotechnology Reports, 2021, 16, 722-731.	0.6	2
8	Charge Transport Mechanism in a Formless Memristor Based on Silicon Nitride. Russian Microelectronics, 2020, 49, 372-377.	0.5	5
9	Silicon Nanocrystals and Amorphous Nanoclusters in SiOx and SiNx: Atomic, Electronic Structure, and Memristor Effects. , 2020, , .		1
10	Charge transport mechanism in La:HfO2. Applied Physics Letters, 2020, 117, .	3.3	11
11	Resistive Switching in Non-Stoichiometric Germanosilicate Glass Films Containing Ge Nanoclusters. Electronics (Switzerland), 2020, 9, 2103.	3.1	15
12	Charge transport mechanism in the metalâ€“nitrideâ€“oxideâ€“silicon forming-free memristor structure. Applied Physics Letters, 2020, 116, .	3.3	24
13	Critical properties and charge transport in ethylene bridged organosilica low-Îº dielectrics. Journal of Applied Physics, 2020, 127, .	2.5	12
14	Electronic structure and charge transport mechanism in a forming-free SiO<i> _x </i>-based memristor. Nanotechnology, 2020, 31, 505704.	2.6	12
15	Nanowired structure, optical properties and conduction band offset of RF magnetron-deposited n-SiIn₂O₃:Er films.. Materials Research Express, 2020, 7, 125903.	1.6	4
16	Charge transport mechanism in periodic mesoporous organosilica low-k dielectric. Applied Physics Letters, 2019, 115, 082904.	3.3	11
17	Charge transport mechanism of high-resistive state in RRAM based on SiO<i>x</i>. Applied Physics Letters, 2019, 114, .	3.3	18
18	Optical properties and charge transport of textured Sc2O3 thin films obtained by atomic layer deposition. Applied Surface Science, 2019, 478, 690-698.	6.1	14

#	Article	IF	Citations
19	Memristor effect in GeO[SiO2] and GeO[SiO] solid alloys films. Applied Physics Letters, 2019, 114, .	3.3	26
20	All Nonmetal Resistive Random Access Memory. Scientific Reports, 2019, 9, 6144.	3.3	24
21	Mechanism of stress induced leakage current in Si3N4. Materials Research Express, 2019, 6, 076401.	1.6	1
22	Charge transport mechanism in SiNx-based memristor. Applied Physics Letters, 2019, 115, 253502.	3.3	21
23	Multiphonon trap ionization transport in nonstoichiometric SiN x. Materials Research Express, 2019, 6, 036304.	1.6	3
24	Swift heavy ion stimulated formation of the Si quantum dots in Si/SiO2 multilayer heterostructures. , 2019, , .		3
25	Electronic structure and charge transport in nonstoichiometric tantalum oxide. Nanotechnology, 2018, 29, 264001.	2.6	16
26	Charge Transport and the Nature of Traps in Oxygen Deficient Tantalum Oxide. ACS Applied Materials & Interfaces, 2018, 10, 3769-3775.	8.0	45
27	Electrophysical properties of Si/SiO2 nanostructures fabricated by direct bonding. Technical Physics Letters, 2016, 42, 590-593.	0.7	3
28	Formation of Si nanocrystals in SiOx, SiOx:C:H films and Si/SiO2multilayer nano-heterostructures by pulse laser treatments. , 2014, , .		1
29	Laser pulse crystallization and optical properties of Si/SiO₂and Si/Si₃N₄multilayer nano-heterostructures. Proceedings of SPIE, 2013, , .	0.8	1
30	Nanoscale Si/SiO<inf>2</inf> double-barrier structures produced by plasma-chemical technology. , 2010, , .		0
31	The electrical properties of MOS-structures with silicon nanoballs incrusted in SiO<inf>2</inf> layer. , 2009, , .		0
32	Nanoscale Si/SiO<inf>2</inf> multilayer structures produced by plasma-chemical technology. , 2009, , .		1